

# Tanner EDA Solutions General MEMS Overview



# Региональный менеджер Mentor Graphics в России

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### **Corporate Overview & History**



SIEMENS Ingenuity for life

- Tanner EDA solutions have been in the market since 1988, 30 years.
- Widely used for analog/mixedsignal ICs and MEMS.
- 1,000+ of customers in 67 countries
- Tanner EDA was acquired by Mentor Graphics March 3, 2015
- Mentor joined Siemens in February, 2017



### **Worldwide Locations**





# **Tanner EDA Solutions Overview**

#### **Analog/Mixed-Signal IC Design**

 A complete analog & mixed-signal IC design environment in one highly-integrated end-to-end flow

#### **MEMS Design and Modeling**

Tanner EDA offers proven, powerful MEMS tools from mask design to 3D model creation for visualization and export to FEM analysis and MEMS-IC co-simulation

- Internet of Things (IoT)
- RF Applications
- MEMS Design & 3D Modeling
- Automotive
- Life Sciences
- Sensors & IC
- Military, Aerospace, Space
- Power Management
- Imaging & Displays
- Consumer Electronics
- Industrial



### How Tanner Tools Address IoT Designs



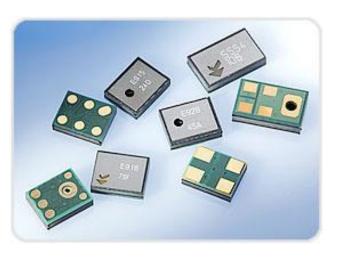
- Top-down design of MEMS, analog, and digital in a single tool flow for all the design on a single die or multiple dies
- Co-design first level packaging of MEMS die and ASIC die
- The MEMS design tool leader with layout features for MEMS including true-curve support, 3D model creation, all-angle & equation based DRC, and co-simulation of MEMS and IC
- Support and PDKs from specialty foundries like X-Fab, TowerJazz, ON-Semi, and **MEMS** fabs Restricted © 2018 Mentor Graphics Corporation





#### **Breakthroughs with Tanner EDA**





"With L-Edit, I can go from concept to finished GDSII in about two weeks. There's never been anything as easy to use as Tanner tools."

Pete Loeppert Vice President R&D Knowles Acoustics



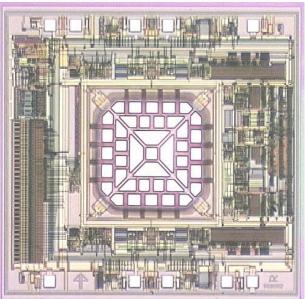


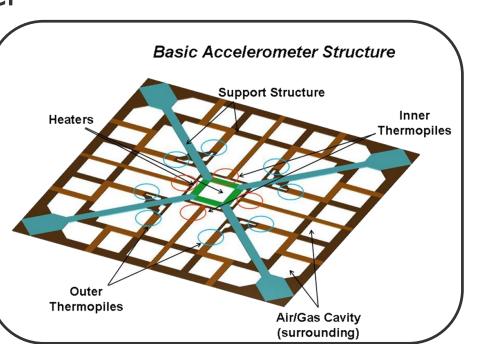


# **Souvenir Olympic Torch by MEMSIC**

- Electronics and MEMS on the same die
- Low cost, high volume, low size, low power

#### **Accelerometer Chip**





Images courtesy of Yongyao Cai, Director, Technology Partnership and Development, MEMSIC, Inc.

#### **Olympic Torch in Action**









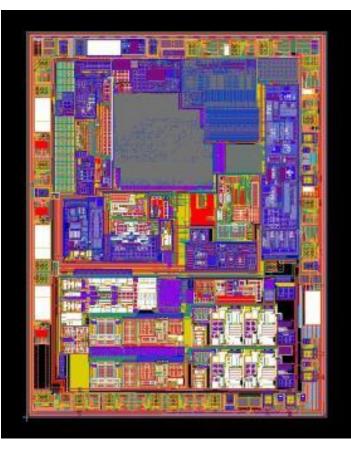
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# **Combining Techniques – TPMS Sensor**

- Single die handles analog,
   ADC, power management,
   digital control, and RF
- Co-designed with MEMS pressure sensor, combined into a single IC package
- Only external components are passives, battery, and antenna





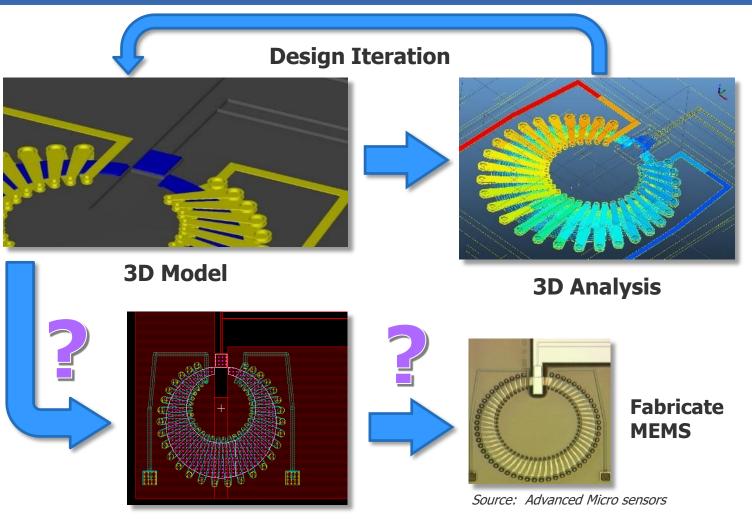
Source: Swindon Silicon Systems



# **MEMS DESIGN FLOW**

# **Design Flow - Other MEMS Tools**

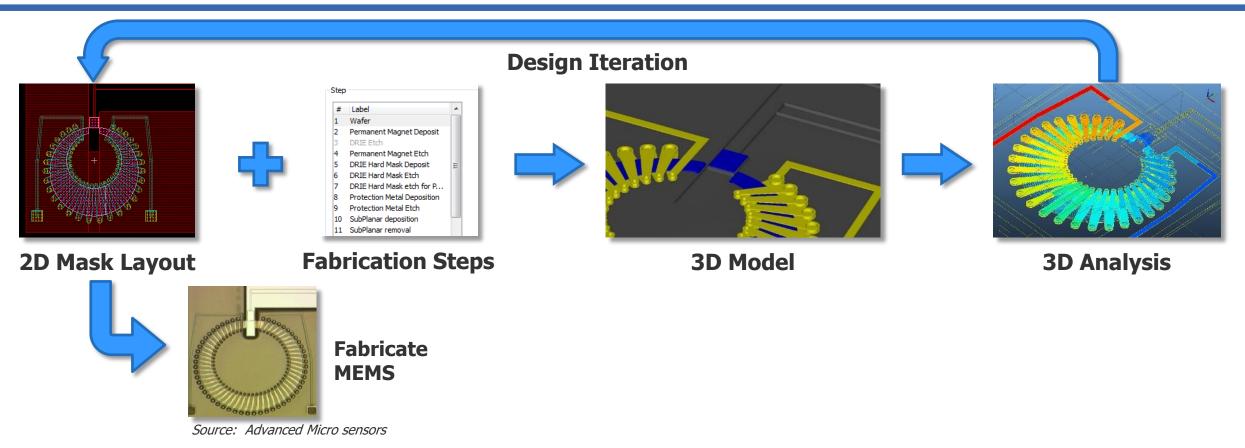
- How Can I Get 2D Layout Masks From My 3D Model?
- How Can I Be Certain My Layout Masks Will Fabricate My 3D MEMS Structure?



2D Mask Layout



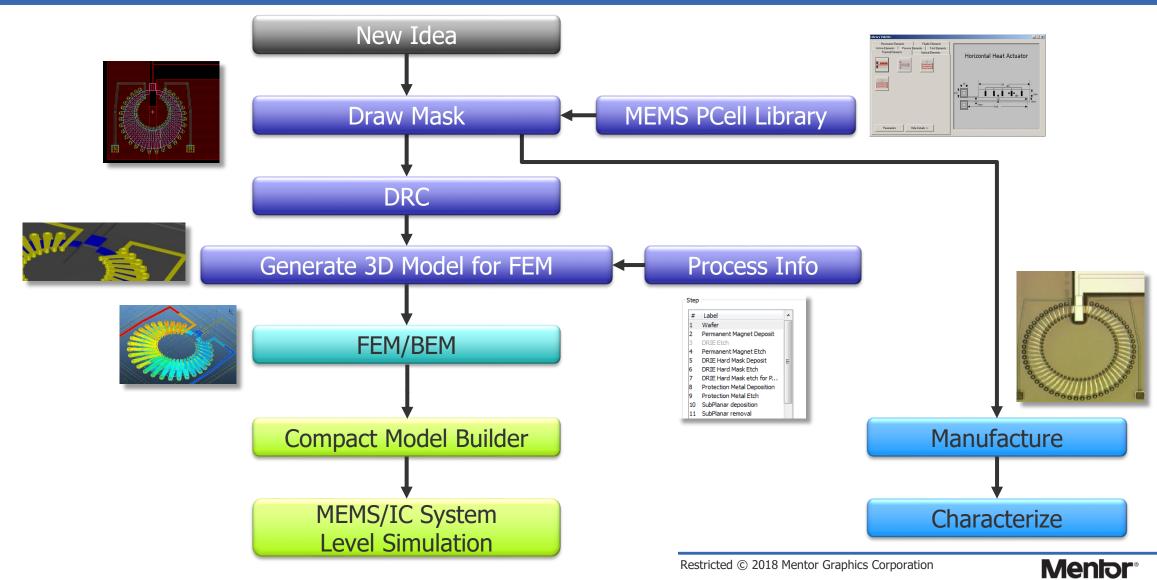
## **Design Flow - Tanner/SoftMEMS**



Always Work From Layout Masks Which Are Used For Fabrication
No Translating The 3D Model To 2D Layout Masks = Less Risk

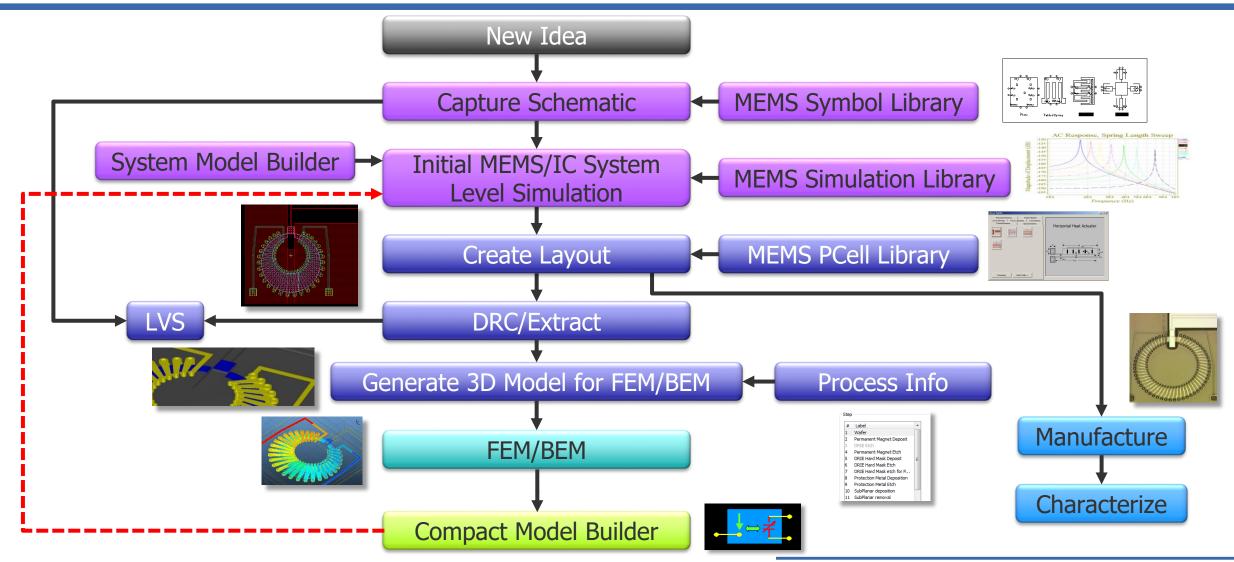


## **MEMS Design Flow – Bottom-Up Methodology**



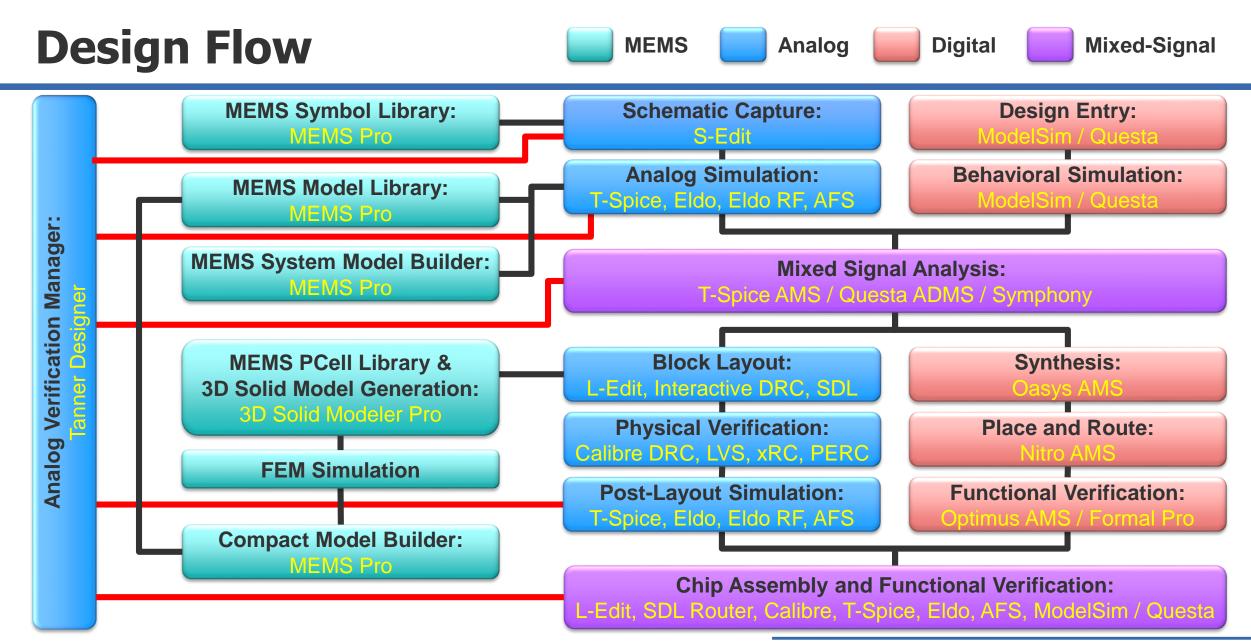
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# **MEMS Design Flow – Top-down Methodology**



Mento



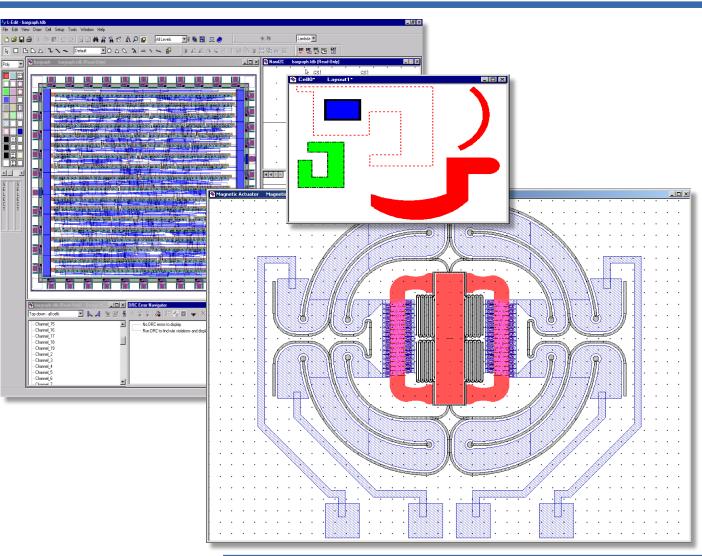




# **MEMS LAYOUT**

# L-Edit MEMS – Full Custom All-Angle Layout Editor

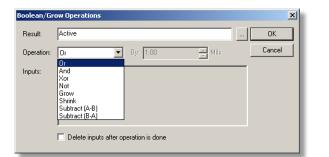
- The Only Tool Developed *Specifically* for MEMS and IC Design
- True Curve Support
- Technology Configurable
- Enhanced Boolean Operations
- Advanced Editing Support:
  - Object Snapping
  - Base Point
  - Alignment
- GDSII, CIF, EPS & DXF support
- Programmable Interface



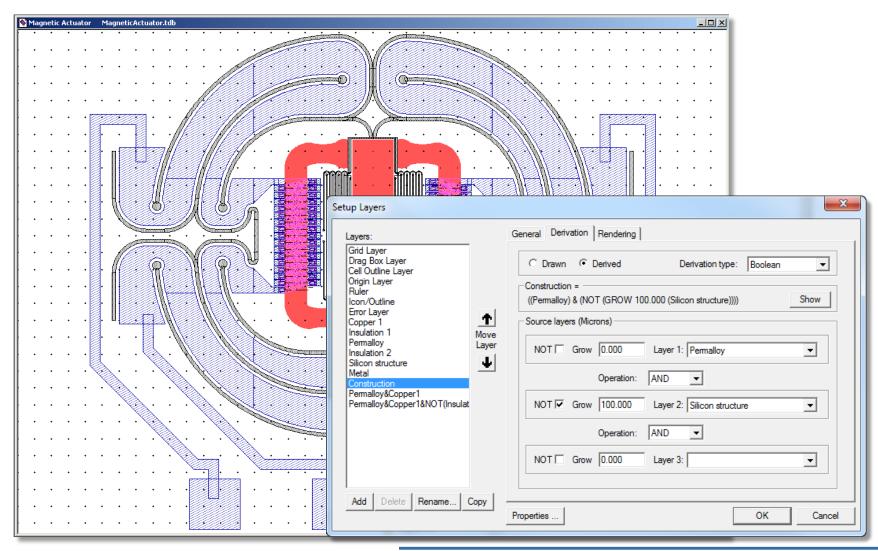
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#### **L-Edit - All-Angle Generate Layers**



Generate Layers	×
Command Sets	Bun
Standard-Derived Layers	Accept
Standard-Derived Layers ✓ Calibre025 5M.drc	
	Cancel
	E dit
Layers to generate	
EXGATE_NP	
✓GATE_L ✓GATE_W	
▼HV_NGATE_W	
HV_PGATE_W	
☑HVN_G0X	
□N_ACT_PW	
NGATE	
Mark All Unmark All	
Automatically mark intermediate layers	
Merge polygons after layer generation	



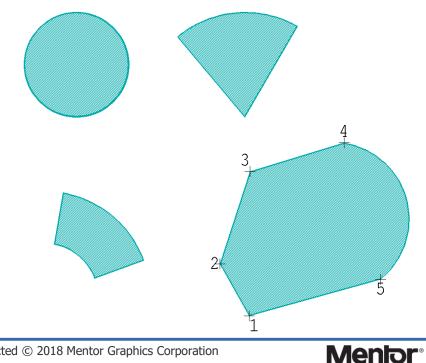


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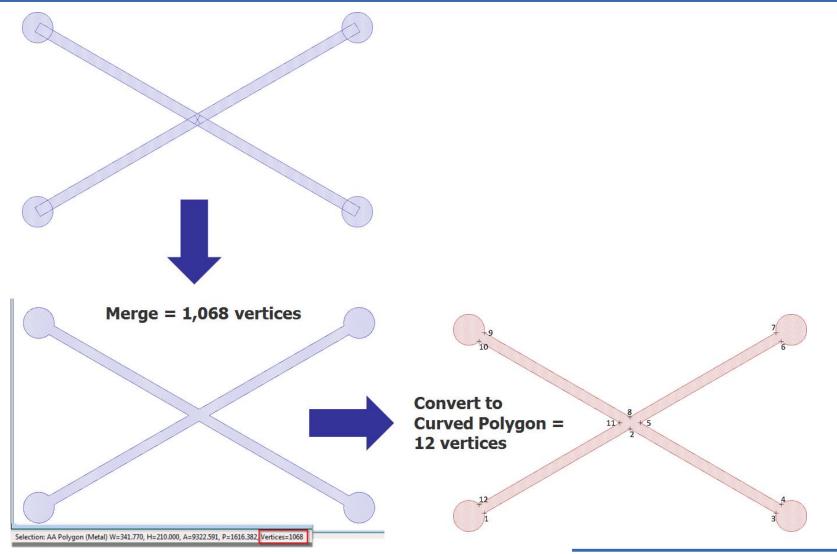
### **Curve Representations**

- True Curved Polygon Representation
- Curved Object Types
- Graphical Editing Comparable With AutoCAD
- Textual Editing Of Curves

Conditates (Microns)       Edit Object(s)         Center       Q n layer: Construct1       Edit Object(s)         Center       S 13000         Badius:       5         Begin:       2000         End:       13000         Badius:       5         Badius:       5         Badius:       5         Badius:       5         Badius:       5	t Object(s)		
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#### **Reconstruct Curves From All-angle Edges**





# L-Edit – Object Snapping and Basepoint

Object Snap

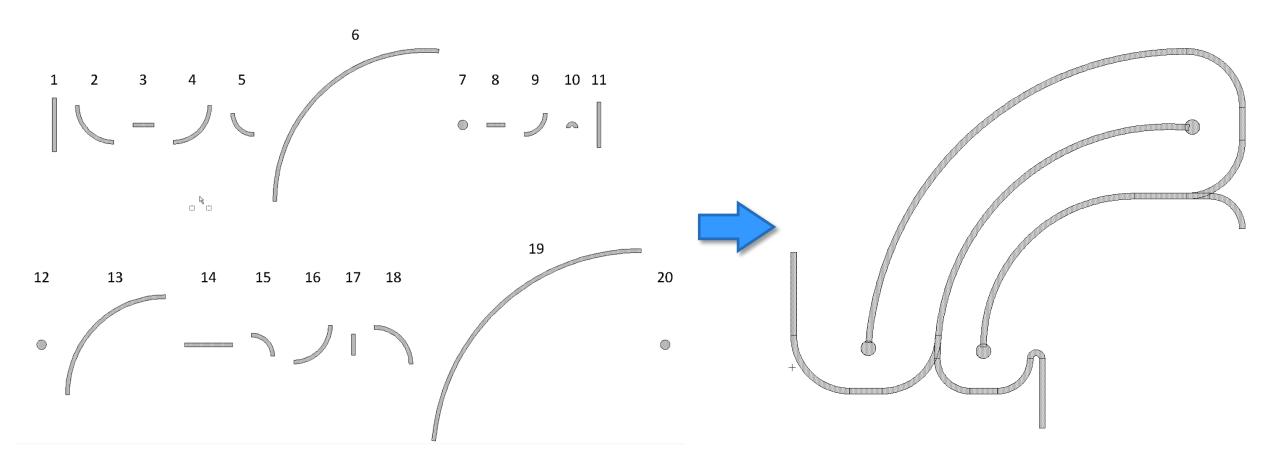
- Snap cursor to object features
  - vertex
  - midpoint
  - edge / centerline
  - intersection
  - center
  - pin (port on instance)
  - instance
- Base Points for Precise
   Positioning

Base Poin	t	×
<u>ି</u> 🗞	26.50 35.00	

Technology       Grid         Object Snap       Interactive DR         Image: Enable Object Snap modes       Image: Object Snap modes         Image: Object Snap modes       Image: Object Snap modes      <	Selection       Drawing       Xref files         C       Node Highlighting       Vias         Instance MBB snapping       Instance MBB       Instance MBB         Abut MBBMBB of objects on the Icon layer       Offset (Microns)         X:       0.000         Y:       0.000         Markers       Image: Color (Markers)         Image: Vias       Vias         Size:       12         pixels
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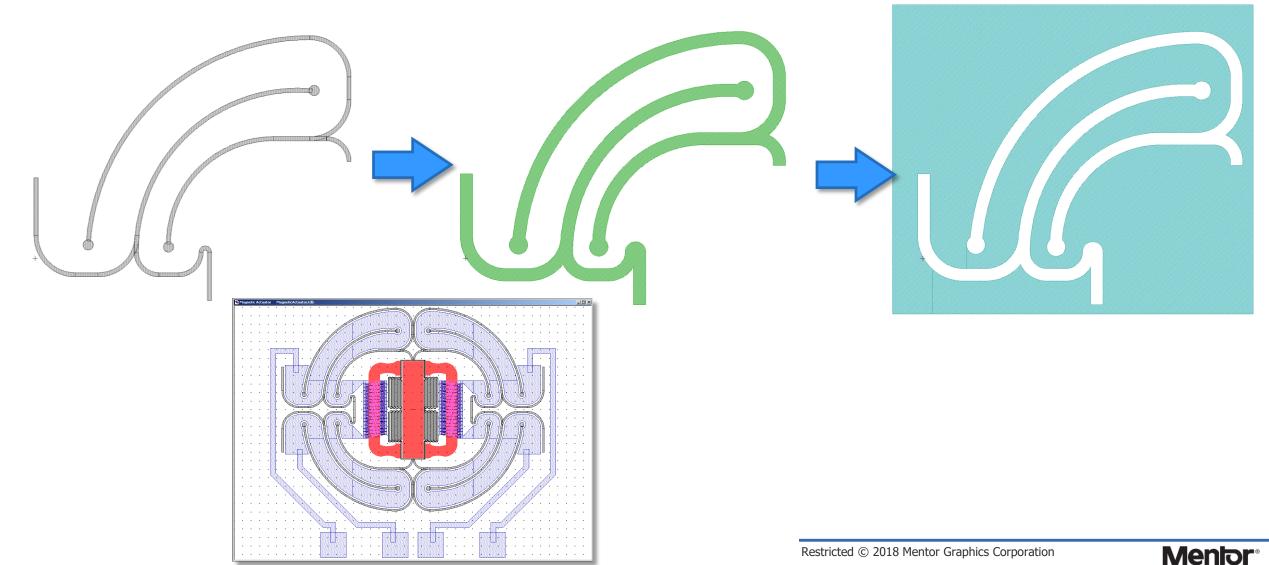


#### **Complex Construction**





#### **L-Edit - All-Angle Generate Layers**

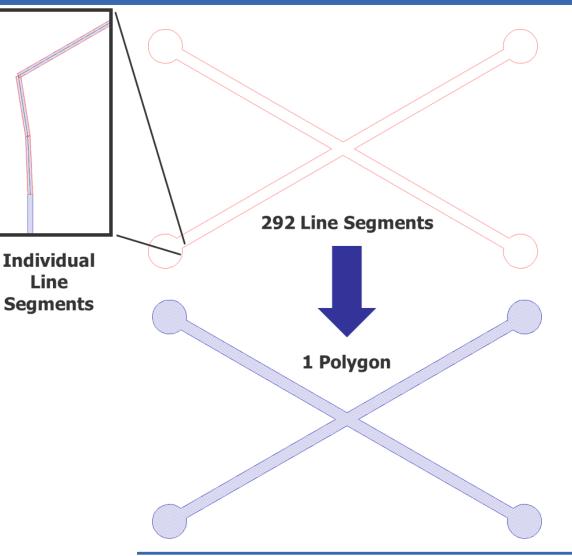


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# **DXF Import/Export**

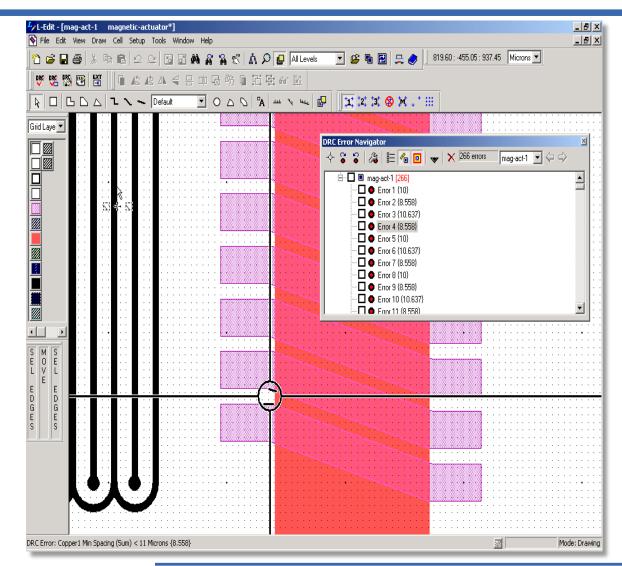
- DXF Import With Boundary Reconstruction
  - Some CAD Tools Fracture
     Polygons Into Edges
     During Export
  - Connects Adjoining Edges
     Within A Tolerance
     Together Into A Filled
     Polygon
  - Can reconstruct curves from a series of all-angle edges





# **L-Edit - DRC for MEMS**

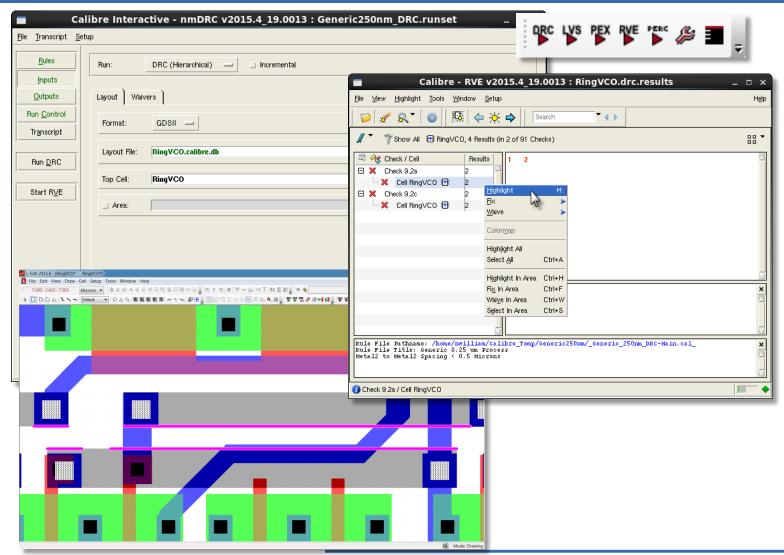
- All Angle Design Rule Checking
- Check for minimum spacing between any type of polygonal objects on various layers.
- Find design flaws immediately!
- Complex DRC rules can be created and customized to meet proprietary MEMS fabrication processes.
- Development and maintenance of technology files easily manageable.





# **Tanner Calibre One**

- Run Calibre nmDRC<sup>™</sup>
   And Calibre nmLVS<sup>™</sup>
   Directly From L-Edit
- Use Calibre RVE<sup>™</sup> To
   View Calibre DRC, LVS,
   And PEX Results In
   L-Edit And S-Edit
- Access to equation based DRC (eqDRC) capability
- Foundry qualified signoff

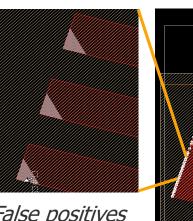


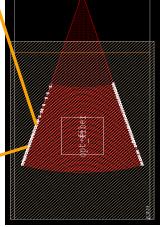


#### DRC

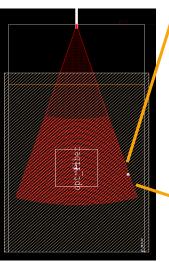
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- Customary IC DRC rules produce large amounts of false errors in MEMS/Photonics designs
- False positive errors can mask the actual design error
- Equation based DRC (eqDRC) solves problem
- MEMS context sensitive rules
- Support device specific rules, e.g., fillets, mechanical rules
- Capture expert knowledge





*False positives from standard DRC run* 





Real Error – need to fix!

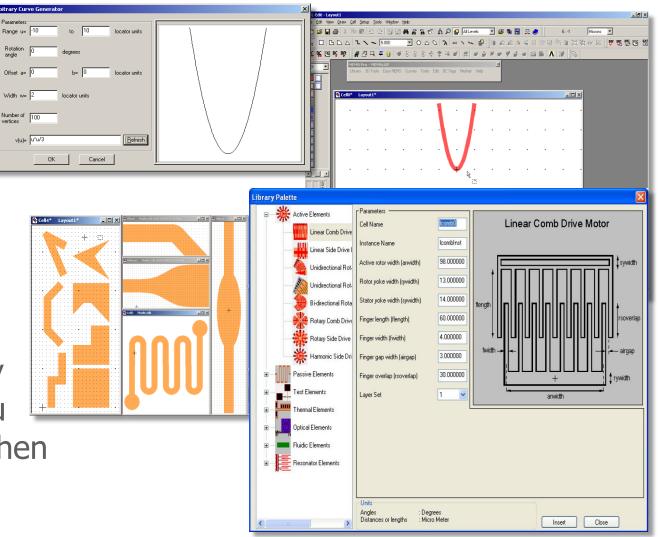


# MEMS LAYOUT TOOLS

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# **SoftMEMS Solid Modeler Pro**

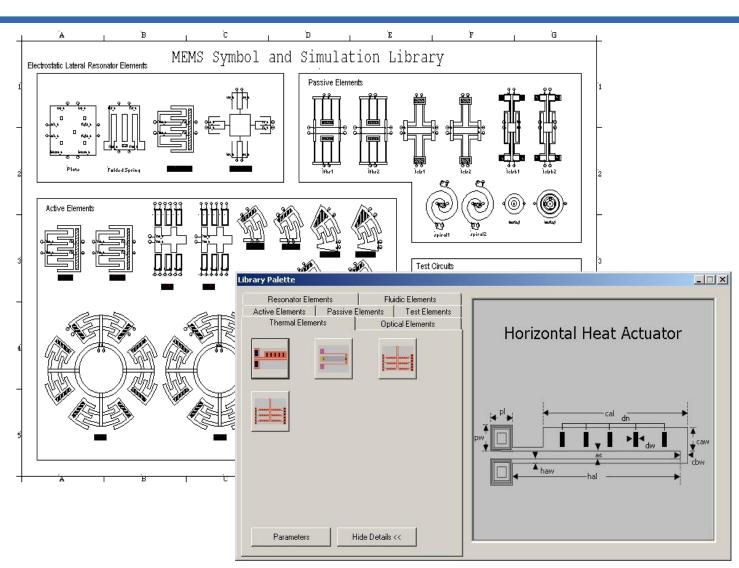
- MEMS toolbar
  - Arbitrary curves
  - Microfluidics and other MEMS technologies
- Easy MEMS
  - MEMS specific tasks such as adding release holes for Plates
- Library Palette
  - Basic layout generators for many MEMS devices creates layout you
     can use as a starting point and then modify for your specific design





# Libraries

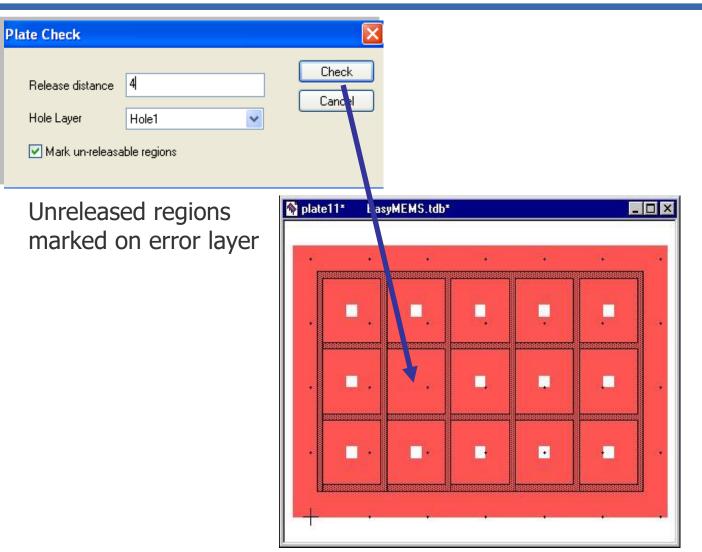
- Supports SPICE, Verilog-A, VHDL-AMS, Matlab
- 3-View System of each component:
  - Schematic
  - Simulation models
  - Parameterized Layout
- Library creation by users with examples from us
- Important to encapsulate design rules in the library





# **Design Rules and Guidelines**

- DRC checks manufacturing rules, spacing, surround, size, etc.
- MEMS context sensitive rules
- Support device specific rules, e.g., fillets, pad rules
- Capture expert knowledge

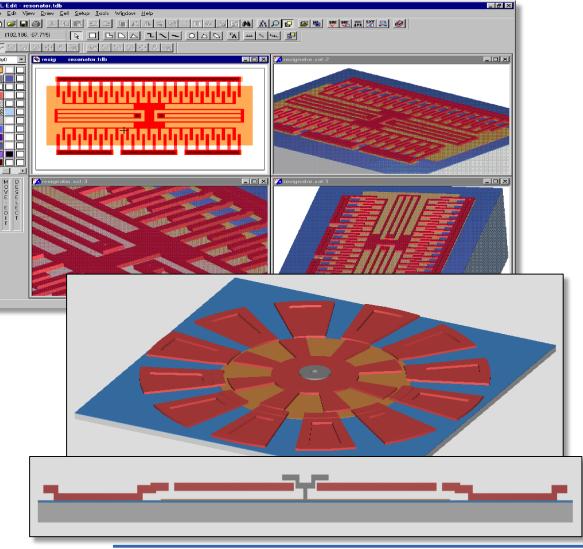




# MEMS 3D TOOLS

# **Solid Modeling with SoftMEMS**

- Create a 3D Solid model from masks and fabrication process description
- Gives 3D graphical representation of MEMS fabrication process
- Embedded in L-Edit
- Multiple views and cross-section
- Snapshot of model can be output
- Output may be sent to FEM/BEM programs for 3D Analysis





# **Fabrication Process Editor**

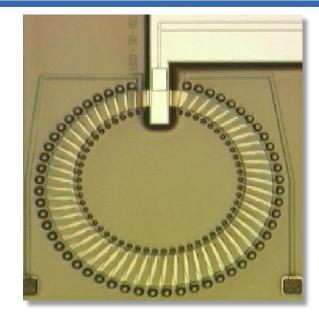
- Describes fabrication processing steps and sequence
- Commands:
  - Wafer manipulation
  - Deposit: Conformal, Snowfall, Fill
  - Etch: Isotropic, Aniostropic, Dry, etc
  - Implant
  - Grow
  - Mechanical Polish
  - Electroplating
  - Wafer Stacking

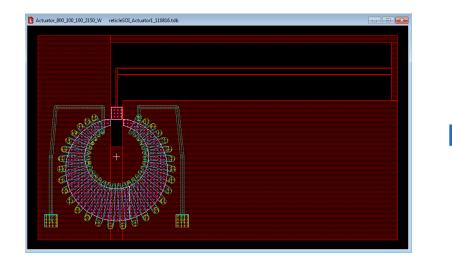
rocess Definition         Process         Name:       MUMPS         Process steps       Step         #       Label         1       Wafer         2       Deposit Nitride         3       Deposit Poly0         4       Etch Poly0         5       Etch Hole0         6       Deposit 0x1         7       Etch Dimple         8       Etch Anchor1         9       Deposit 0x2         11       Etch Poly1         10       Etch Poly1         11       Etch Poly2         12       Deposit 0x2         13       Etch Poly2 Via         14       Etch Poly2         15       Deposit Poly2         16       Etch Poly2         17       Etch Hole2         Image: Enable       Display 3D model for this step	Version: 4.0 Unit: microns			
Add Step Delete Step Comment: Wafer				
Import Export OK Cancel				

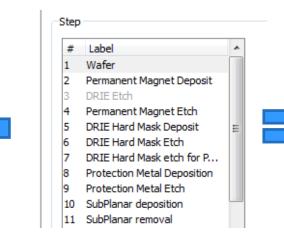


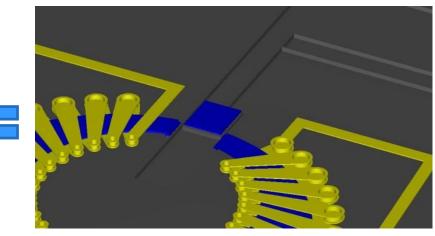
# Mask/Process Co-design

- Designers and process engineers collaborate
- Process compatibility checked
- Find fabrication issues
- Communicate between fab & design house
- Predict shape, predict performance







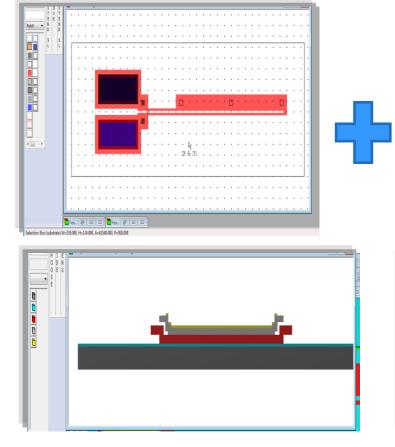


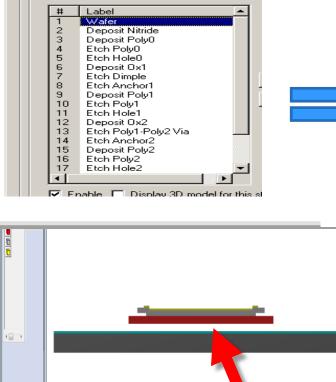


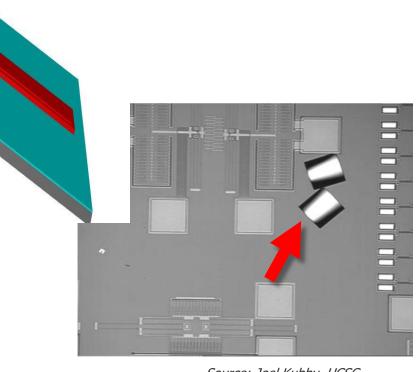
# **Virtual Prototyping**

- New designers can learn
- Example: Improperly anchored Pad

Step-







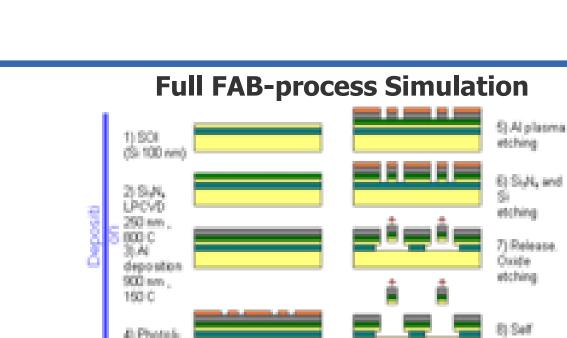
Source: Joel Kubby, UCSC

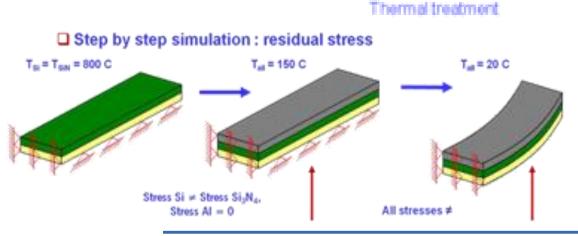
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### **Material Properties**

- Material properties depend on deposition conditions unique to fab process
- Pre-stress in materials effect performance
- Important to simulate using the correct material properties
- CAD can help to characterize materials



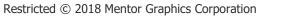




RTA BOL

### **Package Modeling**

- MEMS package determines device performance
- Co-Design MEMS + Package
- Energy Harvester
  - Visual The Device
  - Communicate With The Fab
  - Create 3D Model of MEMS And Package For FEM Analysis
  - Virtual Prototyping
  - Coupled Fluid-Mechanical-Piezo-Electric Simulation

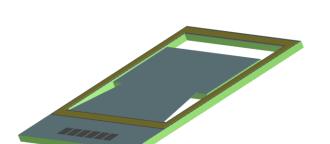


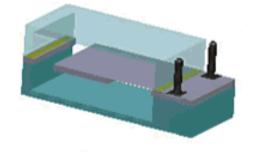


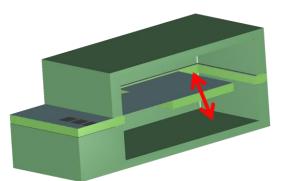




The harvester is near the middle of this viev



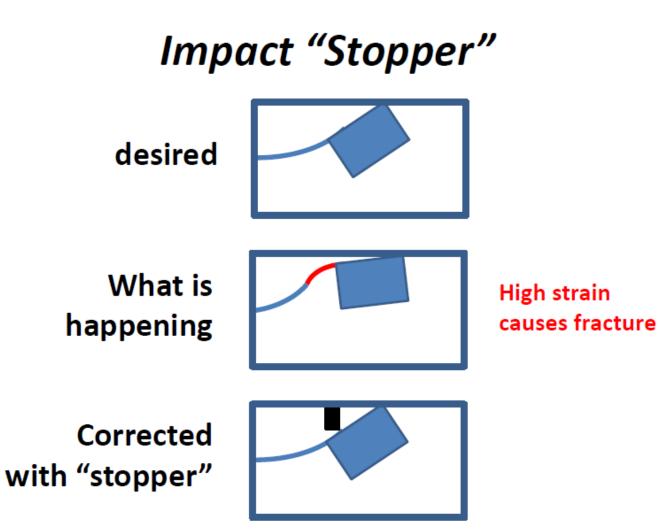


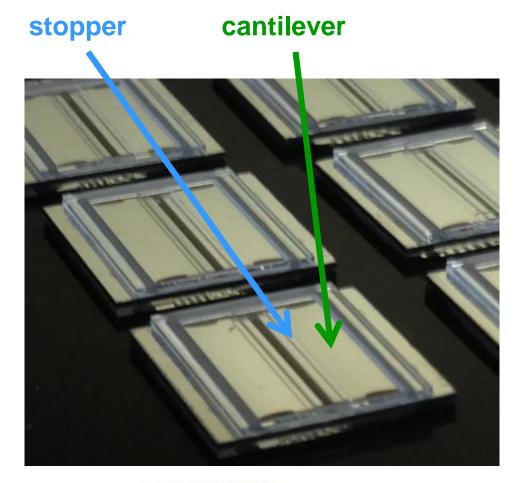




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### **MEMS Packaging – Mechanical Robustness**





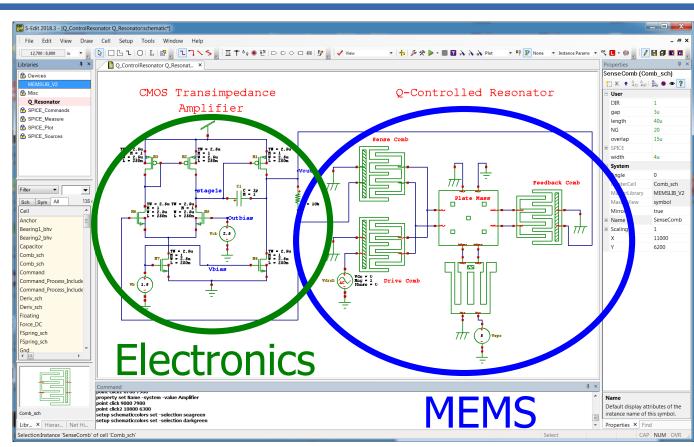
softMEMS Source: MicroGen



### SYSTEM LEVEL SIMULATION

### **MEMS & IC Co-Simulation**

- Schematics can contain both IC & MEMS Devices
- IC modeled using standard TSMC IC SPICE models
- MEMS modeled using behavioral descriptions with mechanical, electrostatic, magnetic, fluidic disciplines
- MEMS models

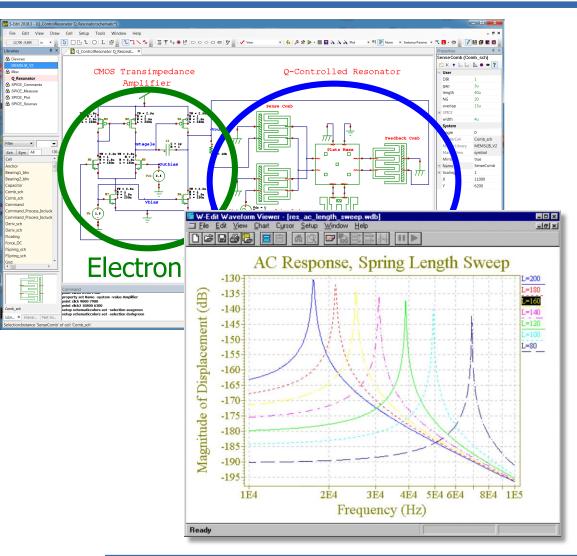


- No universal primitives as in digital design
- Primitives may exist in application areas –
   i.e. beam, gaps, plate
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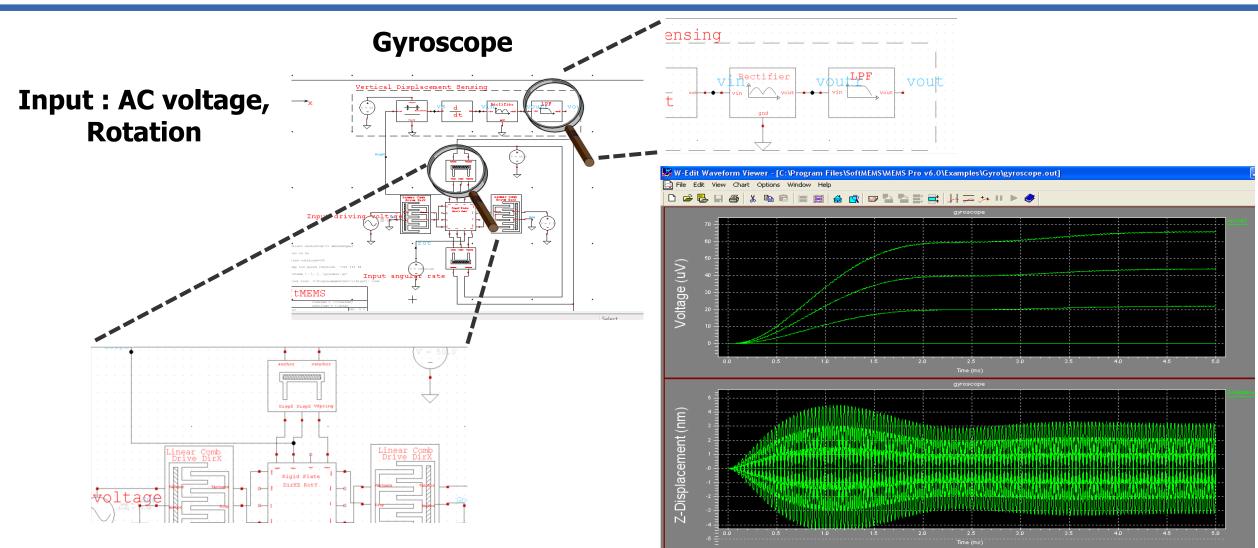
### **Approach to System Modeling**

- Models can be used in T-Spice
  - No universal primitives as in digital design
  - Primitives may exist in application areas – i.e. beam, gaps, plate
- Create libraries of models when possible
- Supports Parametric, Transient, AC, and Noise Analysis
- Describe models with
  - SPICE
  - Verilog-A





### **System Modeling- Circuits and Sensors**



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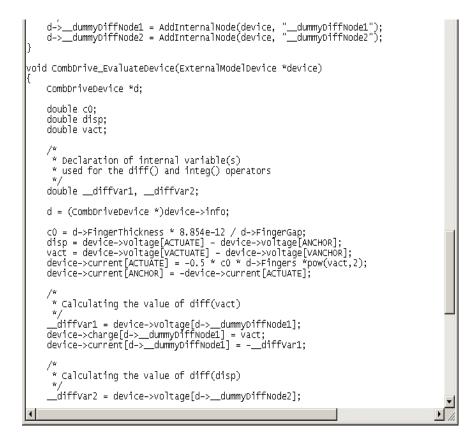


### **MODEL BUILDER**

### **System Model Builder**

Creates a model ready for simulation from analytical equations
Outputs model in SPICE, C, Verilog-A, or VHDL-AMS

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Pins/Para	meters	Equation	n Editor		
				] = [	
atan tan	asin sin	acos	e^x In	10^x	: Parameter Name Variable Name
tan		COS	In	log	anchor Fingers c0
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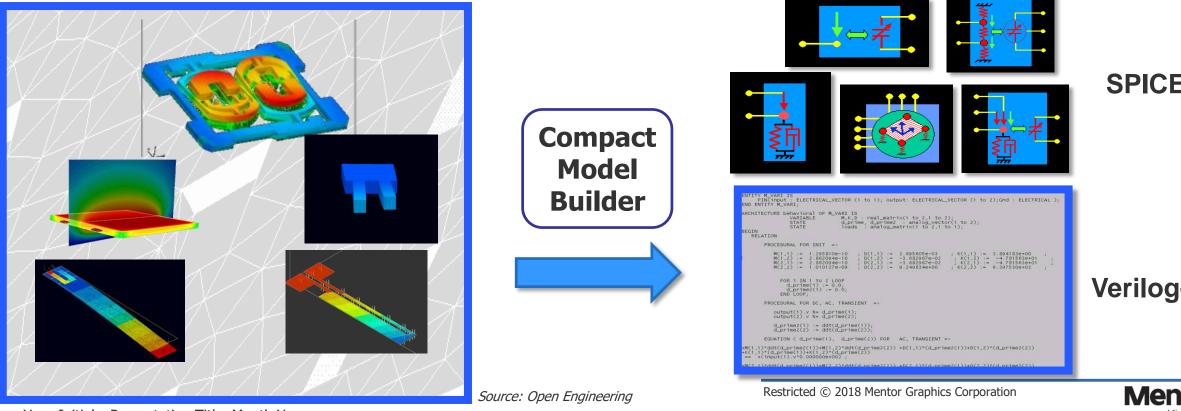


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### **Compact Model Creation**

- MEMS must be analyzed in 3D
- Translate Results From A Coupled-Finite Element/Boundary **Element Model Simulation To Behavioral Model**

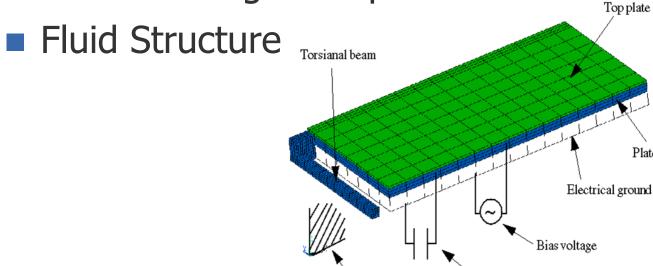


#### SPICE

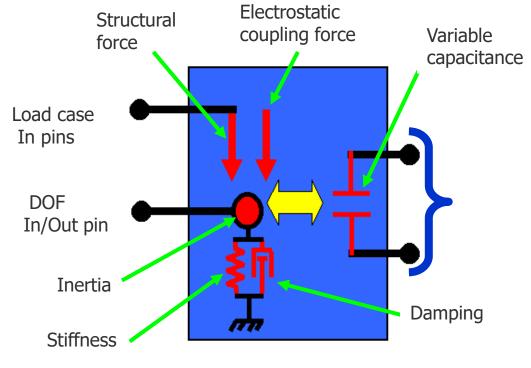
#### **Verilog-A**

### **Compact Model Builder**

- Reduced Order Model Generation From FEM Results
- Handles Coupled Electrostatic-Structural Reduction
- Handles Multiple Degrees Of Freedoms
- Linear Combination of Models
- Pull-In Voltage Computation



Plane of symetry (xz)

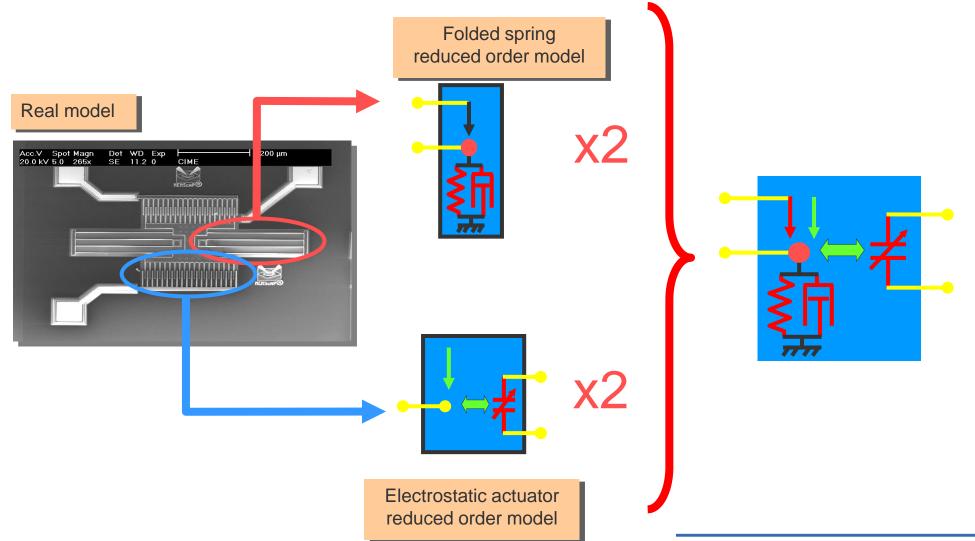


Me

Plate

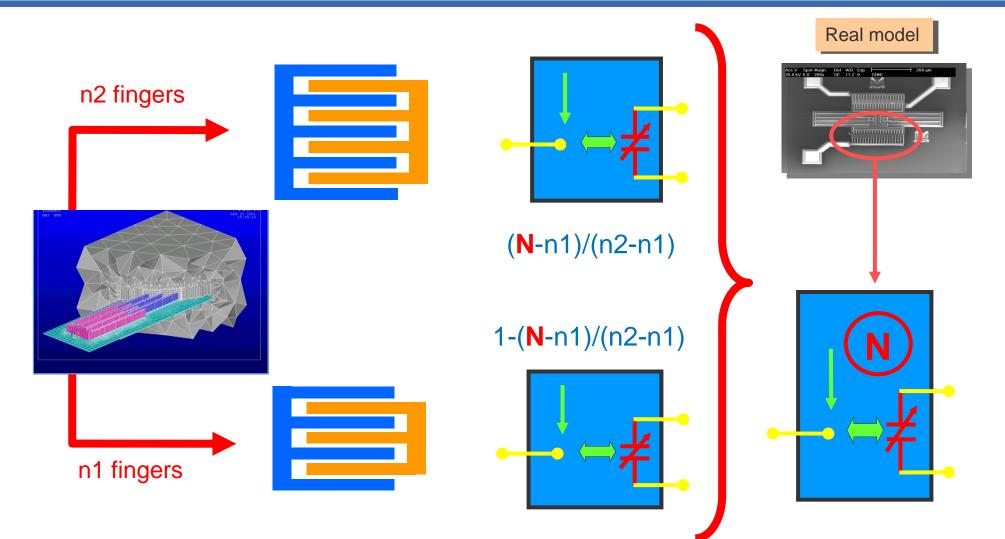
Computed capacitance

### **Compact Model Builder-Assembly**





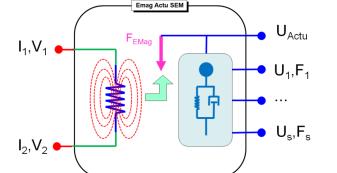
### **Compact Model Builder-Parametric models**



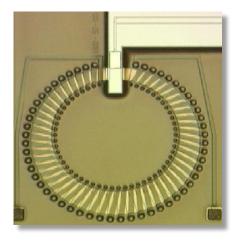


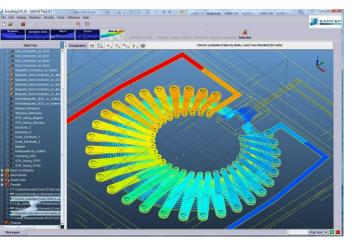
### **Example-Coupled Magnetic-Mechanical MEMS**

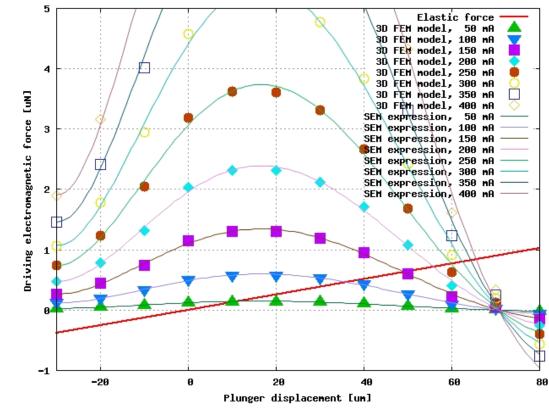
- Magnetic Actuator
- Couple magnetics to mechanics
- Enable system simulation



System design trade-offs







Source: Advanced Micro sensors



### **DESIGN KITS FOR MEMS**

### **Document Fabrication Process**

Creates HTML document from Process Description showing materials used and a cross-section of each fabrication step
Process Documentation for: PolyMUMPs :

Etch Poly0 SoftMEMS MEMS Pro Library 3D Tools 2D Tools Easy M Technology Manager Date of generation: 03/23/17 16:53:32 3D Process Steps Edit Material Database General Layers Materials Preset Wafers Deposit Metal Detect True Curves Show Intermediate Units: micron Edit Preset Wafers Foundry: SoftMEMS Sten Edit Process Definition **Author: SoftMEMS** # Label Step Name: Wafe Document Process Wafer Command: Wafer **Organization: SoftMEMS** Deposit Poly0 Mechanical Polish Etch Poly0 Export Process to EXCEL Deposit Metal Wafer ID: W1 **Revision No: 1.00** Mechanical Polis Deposit Poly1 Use preset Wafer: Set 3D Area **Units System: SI** Etch Poly1 Sacrificial Etch Mask Name: substrate Clear 3D Area Deposit Metal Units for steps: micron Deposit Poly1 Target View 3D Model Fixed Thicknes View Cross Section **Materials List** Defeature 3D Model Delete Model Etch Poly1 Substrate Export 3D Model Poly0 -Enable Poly0 + Add Step Sacrificial Etch Metal Comment: This is a wafe Poly1 Deposit Metal 

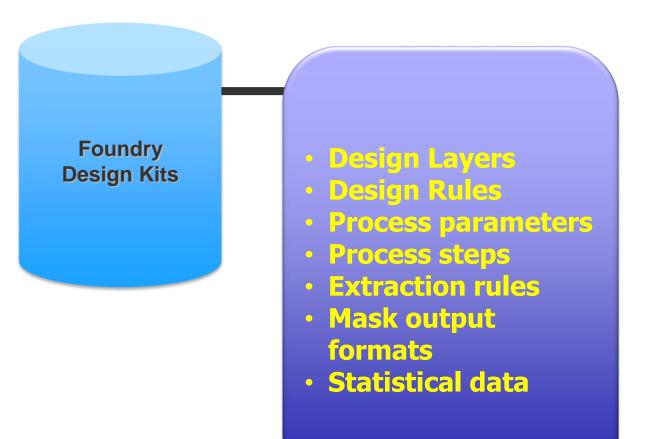


Wafer Step

Deposit Poly0

### **Design Kits**

- Standardize information exchange, even if not for standard process
- Modeling formats, material properties, design rules
- Tech Transfer success the more that is documented the higher success rate





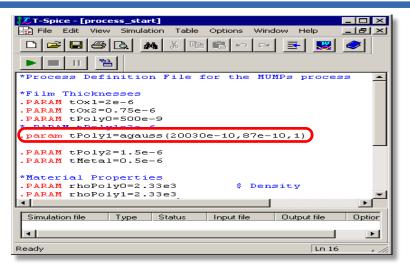
### DESIGN FOR MANUFACTURABILITY FOR MEMS

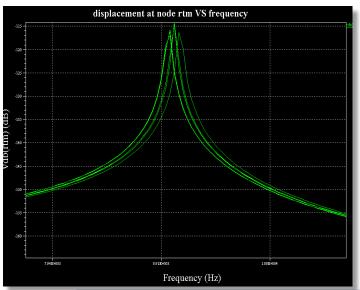
### **Statistical Analysis**

- Statistical analysis based on process/mask variations
  - Incorporates statistical data from foundries
  - Monte Carlo, Yield analyses

#### Enables users to:

- Develop process corners for simulation
- Design centering
- Calculate sensitivity



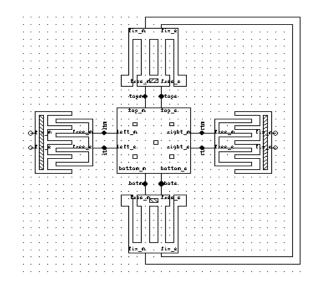


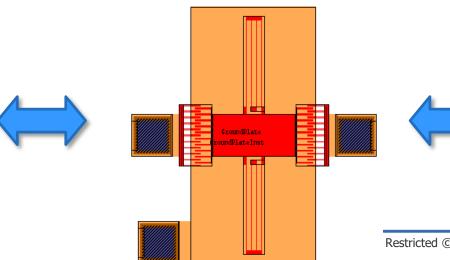
Restricted © 2018 Mentor Graphics Corporation

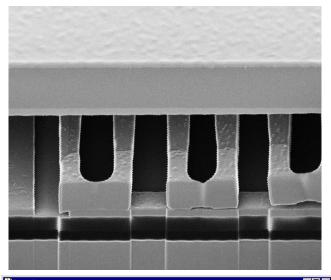


### **Parasitic Extraction and LVS**

- MEMS devices must be simulated with their environment
- Problems occur if details left out
- Parasitics in multiple energy domains: thermal, electronic etc.
- Re-simulate after extraction of parasitics
- Create "multi-physics" netlist with parasitics included





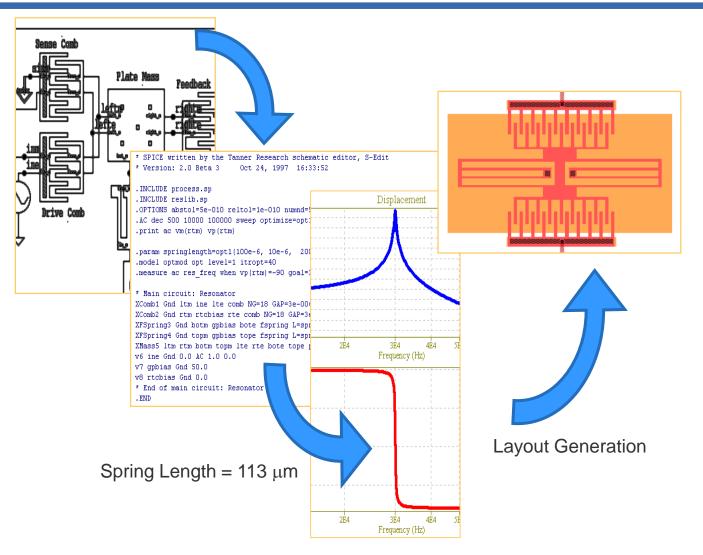


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### **Design for Manufacturing**

- Process and Mask Design changes to Improve Yield
- Sensitivity-What parameters need to be controlled?
- Design Centering- Variation Tolerant designs
- Design Optimization used to generate layout that is most tolerant



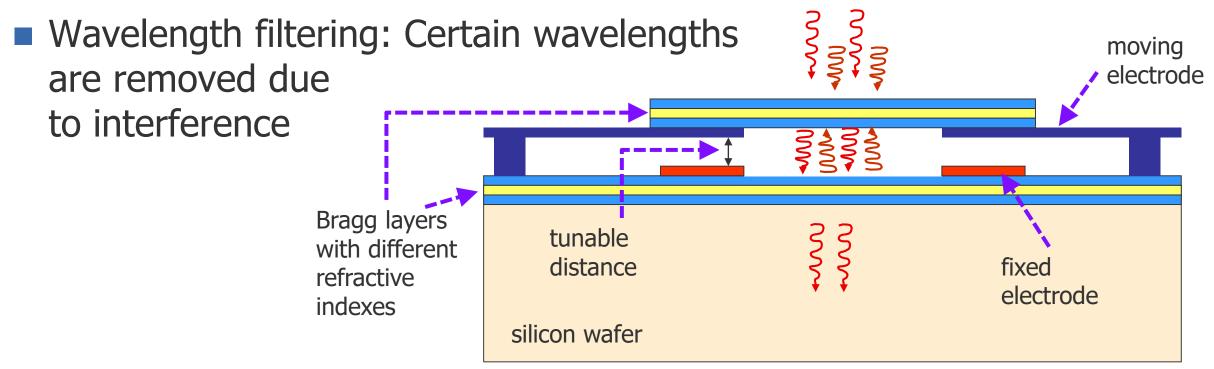




### **Tunable Filter for WDM Applications**

### Tunable filtering:

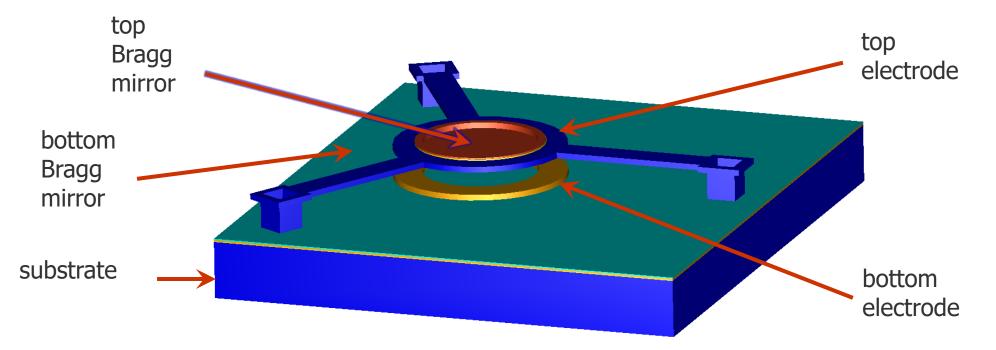
- The distance between two mirrors determines the range of frequencies that are filtered out
- The distance between two mirrors is controlled by electrostatic actuation





### **Tunable Filter 3D Design**

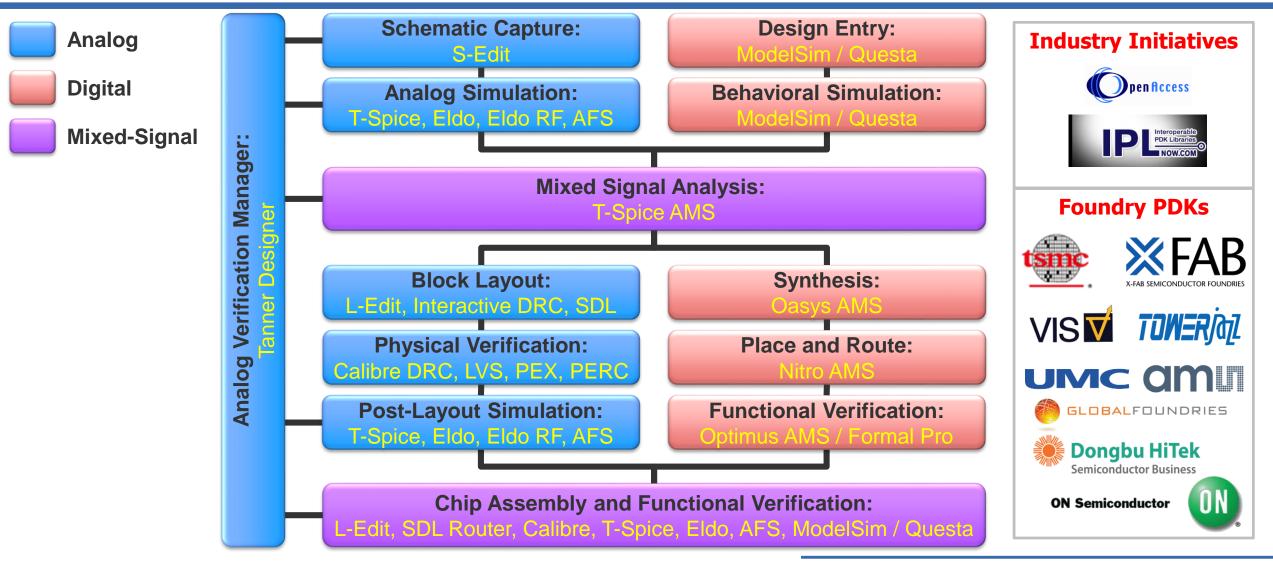
- Top electrode: metal ring suspended on three support arms
- Bottom electrode: polysilicon ring
- Top/bottom mirrors: layers of polysilicon, oxide, and nitride





### IC TOOL FLOW

### **Design Flow**





### **Contact Information**

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